



STB11N65M5, STD11N65M5, STF11N65M5, STP11N65M5, STU11N65M5

N-channel 650 V, 0.43 Ω typ., 9 A MDmesh™ V Power MOSFET in D²PAK, DPAK, TO-220FP, TO-220 and IPAK packages

Datasheet — production data

Features

Order codes	V _{DSS} @ T _{Jmax}	R _{DS(on)} max	I _D
STB11N65M5	710 V	< 0.48 Ω	9 A
STD11N65M5			
STF11N65M5			
STP11N65M5			
STU11N65M5			

- Worldwide best R_{DS(on)} * area
- Higher V_{DSS} rating and high dv/dt capability
- Excellent switching performance
- 100% avalanche tested

Applications

- Switching applications

Description

These devices are N-channel MDmesh™ V Power MOSFETs based on an innovative proprietary vertical process technology, which is combined with STMicroelectronics' well-known PowerMESH™ horizontal layout structure. The resulting product has extremely low on-resistance, which is unmatched among silicon-based Power MOSFETs, making it especially suitable for applications which require superior power density and outstanding efficiency.

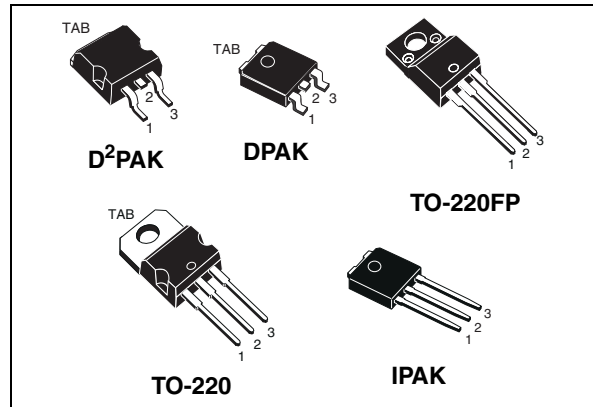
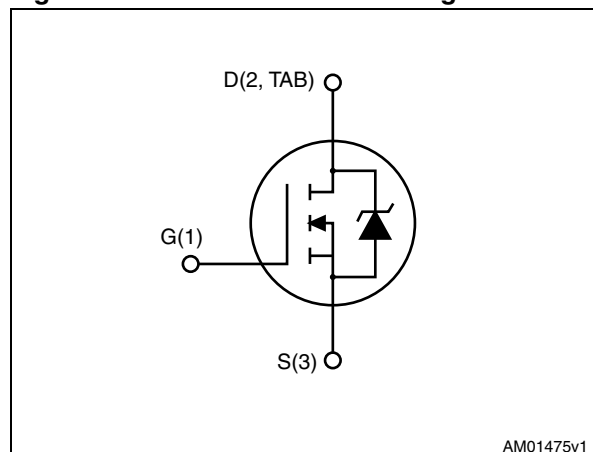


Figure 1. Internal schematic diagram



AM01475v1

Table 1. Device summary

Order codes	Marking	Package	Packaging
STB11N65M5	11N65M5	D ² PAK	Tape and reel
STD11N65M5		DPAK	
STF11N65M5		TO-220FP	Tube
STP11N65M5		TO-220	
STU11N65M5		IPAK	

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		D ² PAK DPAK TO-220 IPAK	TO-220FP	
V _{GS}	Gate-source voltage	± 25		V
I _D	Drain current (continuous) at T _C = 25 °C	9	9 ⁽¹⁾	A
I _D	Drain current (continuous) at T _C = 100 °C	5.6	5.6 ⁽¹⁾	A
I _{DM} ⁽¹⁾	Drain current (pulsed)	36	36 ⁽¹⁾	A
P _{TOT}	Total dissipation at T _C = 25 °C	85	25	W
dv/dt ⁽²⁾	Peak diode recovery voltage slope	15		V/ns
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; T _C = 25 °C)	2500		V
T _{stg}	Storage temperature	- 55 to 150		°C
T _j	Max. operating junction temperature	150		°C

- Limited by maximum junction temperature.
- I_{SD} ≤ 9 A, di/dt ≤ 400 A/μs; V_{DS peak} < V_{(BR)DSS}, V_{DD}=400 V

Table 3. Thermal data

Symbol	Parameter	Value					Unit
		D ² PAK	DPAK	TO-220FP	TO-220	IPAK	
R _{thj-case}	Thermal resistance junction-case max	1.47		5.0	1.47		°C/W
R _{thj-pcb} ⁽¹⁾	Thermal resistance junction-pcb max	30	50				°C/W
R _{thj-amb}	Thermal resistance junction-ambient max			62.5		100	°C/W

- When mounted on 1 inch² FR-4, 2 Oz copper board.

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I _{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T _{jmax})	2	A
E _{AS}	Single pulse avalanche energy (starting t _j =25°C, I _d = I _{AR} ; V _{dd} =50)	130	mJ

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 5. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}, V_{GS} = 0$	650			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 650\text{ V}$ $V_{DS} = 650\text{ V}, T_C = 125\text{ °C}$			1 100	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 25\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 4.5\text{ A}$		0.43	0.48	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}, f = 1\text{ MHz},$ $V_{GS} = 0$	-	644	-	pF
C_{oss}	Output capacitance			18		
C_{rss}	Reverse transfer capacitance			2.5		
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{DS} = 0\text{ to }520\text{ V}, V_{GS} = 0$	-	55	-	pF
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related			17		
R_G	Intrinsic gate resistance	$f = 1\text{ MHz open drain}$	-	5	-	Ω
Q_g	Total gate charge	$V_{DD} = 520\text{ V}, I_D = 4.5\text{ A},$ $V_{GS} = 10\text{ V}$ (see Figure 20)	-	17	-	nC
Q_{gs}	Gate-source charge			4.6		
Q_{gd}	Gate-drain charge			8.5		

1. Time related is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}
2. Energy related is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(v)}$	Voltage delay time	$V_{DD} = 400\text{ V}$, $I_D = 7.5\text{ A}$,		23		ns
$t_{r(v)}$	Voltage rise time	$R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$	-	10	-	ns
$t_{f(i)}$	Current fall time	(see Figure 21 and		13.5		ns
$t_{c(off)}$	Crossing time	Figure 24)		13		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		9	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		36	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 9\text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 9\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	-	232		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 100\text{ V}$ (see Figure 21)		2		μC
I_{RRM}	Reverse recovery current			17.5		A
t_{rr}	Reverse recovery time	$I_{SD} = 9\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	-	328		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 100\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$		2.8		μC
I_{RRM}	Reverse recovery current	(see Figure 21)		17		A

1. Pulse width limited by safe operating area.

2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for DPAK and IPAK

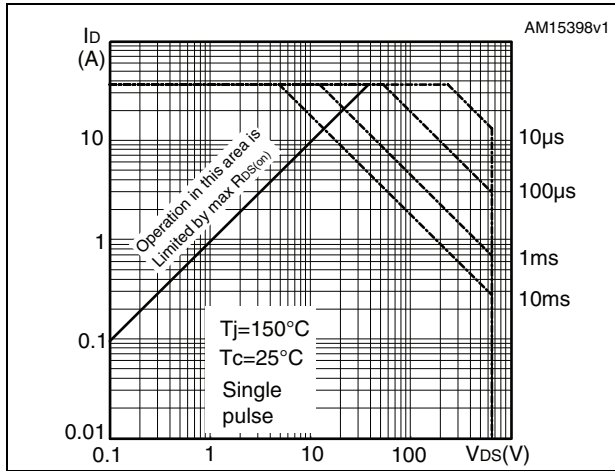


Figure 3. Thermal impedance DPAK and IPAK

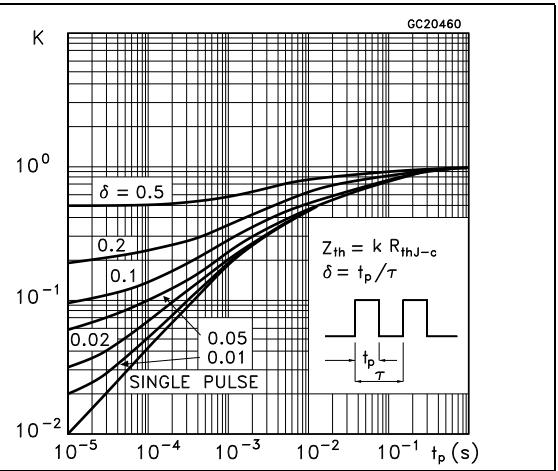


Figure 4. Safe operating area for TO-220FP

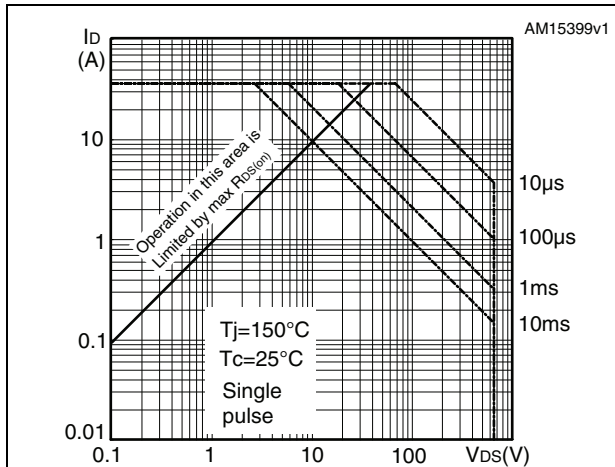


Figure 5. Thermal impedance for TO-220FP

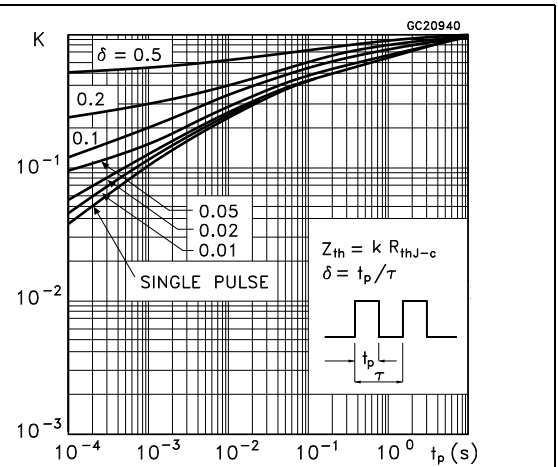


Figure 6. Safe operating area for TO-220 and D²PAK

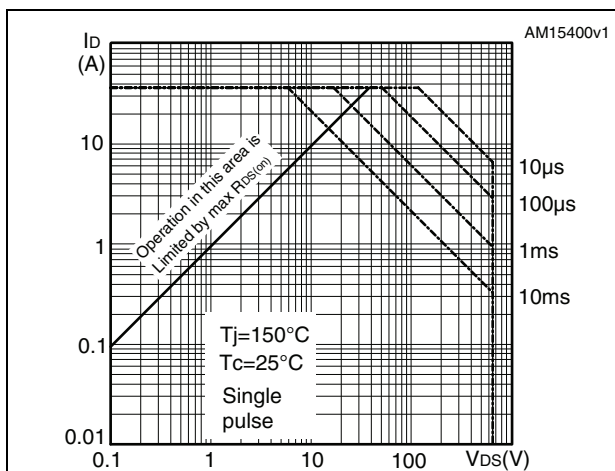


Figure 7. Thermal impedance for TO-220 and D²PAK

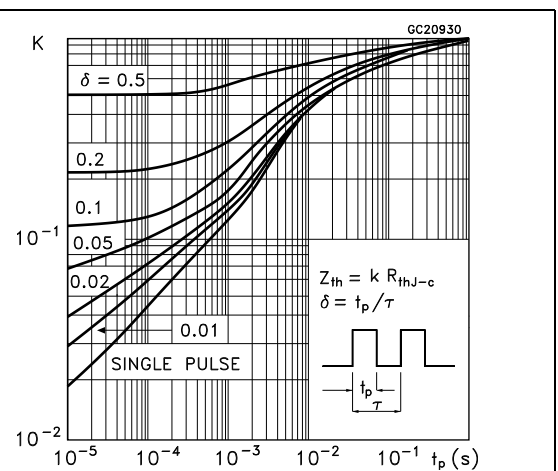


Figure 8. Output characteristics

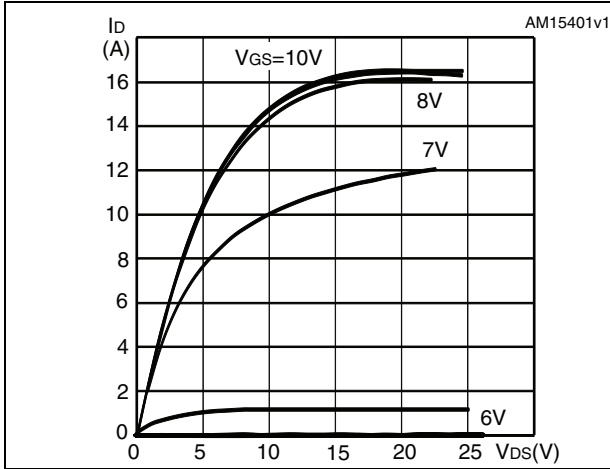


Figure 9. Transfer characteristics

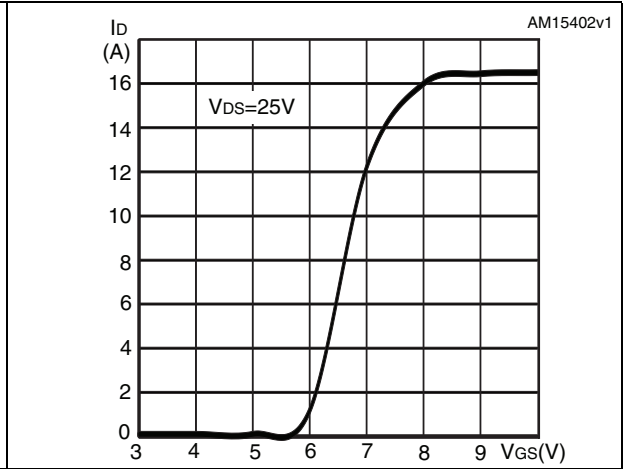


Figure 10. Gate charge vs gate-source voltage

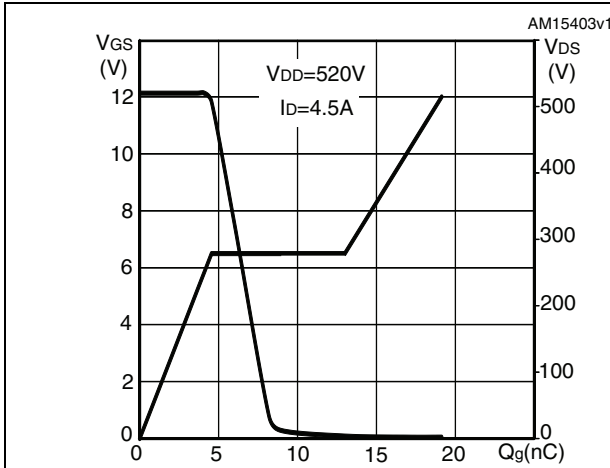


Figure 11. Static drain-source on-resistance

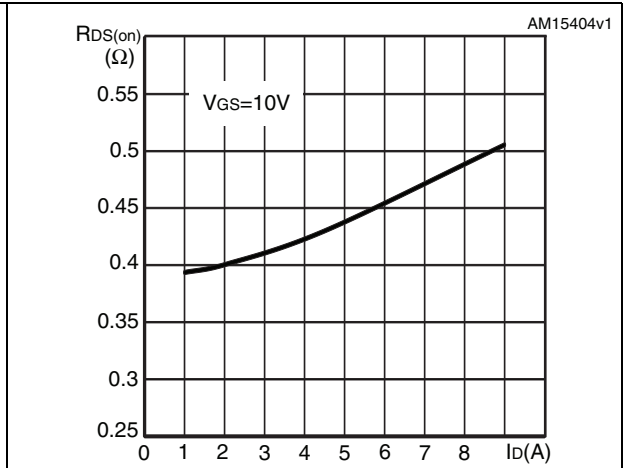


Figure 12. Capacitance variations

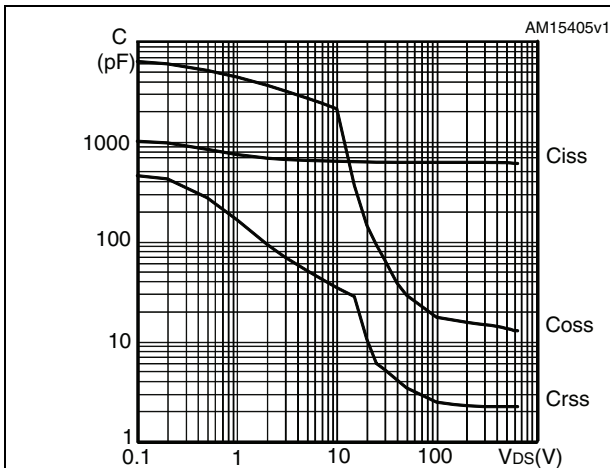


Figure 13. Output capacitance stored energy

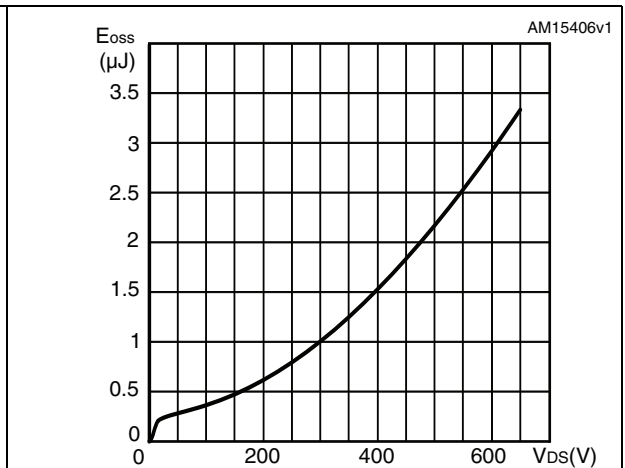


Figure 14. Normalized on-resistance vs temperature

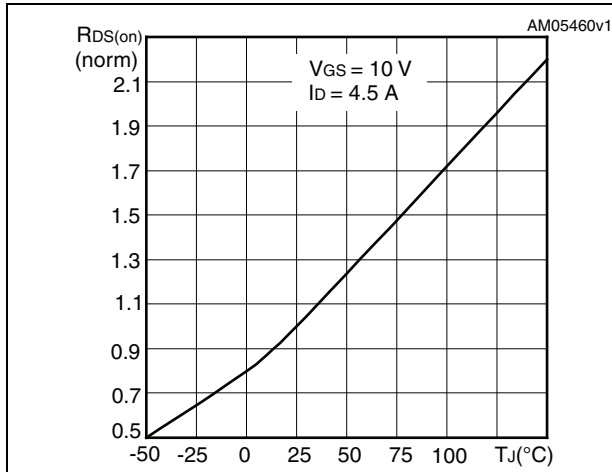


Figure 15. Normalized gate threshold voltage vs temperature

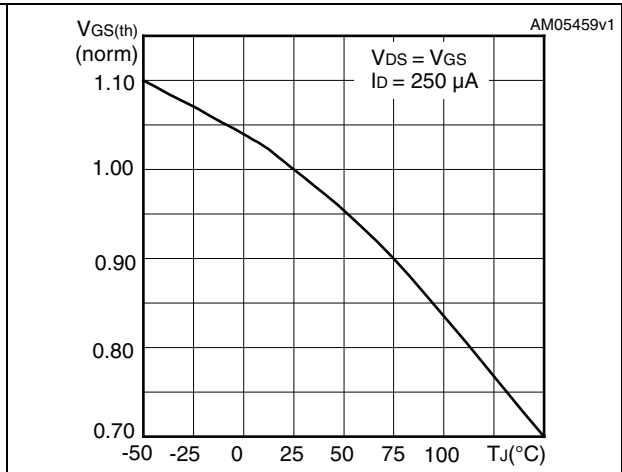


Figure 16. Drain-source diode forward characteristics

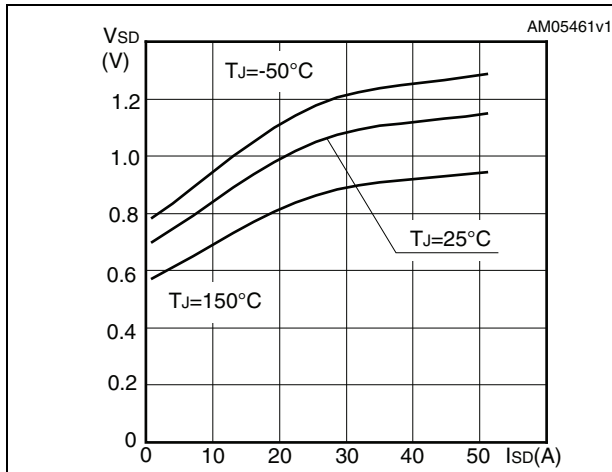


Figure 17. Normalized B_{VDS} vs temperature

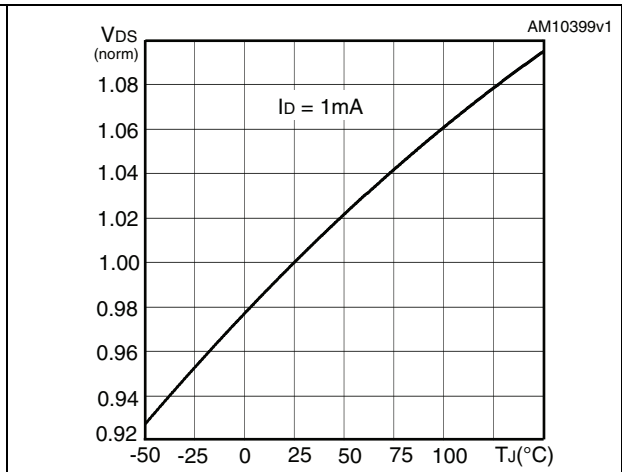
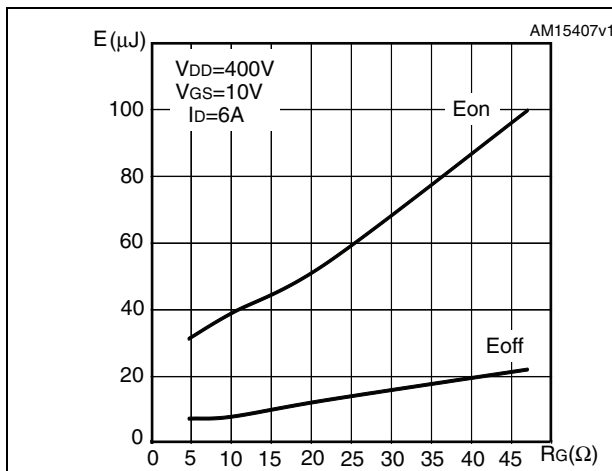


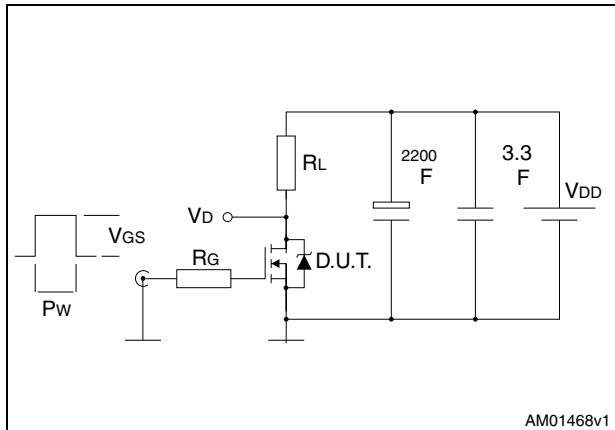
Figure 18. Switching losses vs gate resistance⁽¹⁾



1. Eon including reverse recovery of a SiC diode

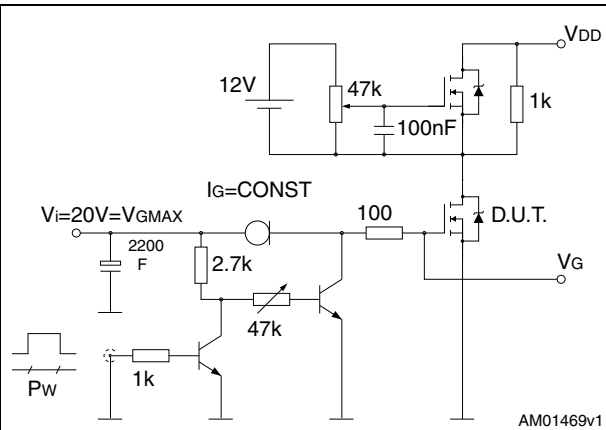
3 Test circuits

Figure 19. Switching times test circuit for resistive load



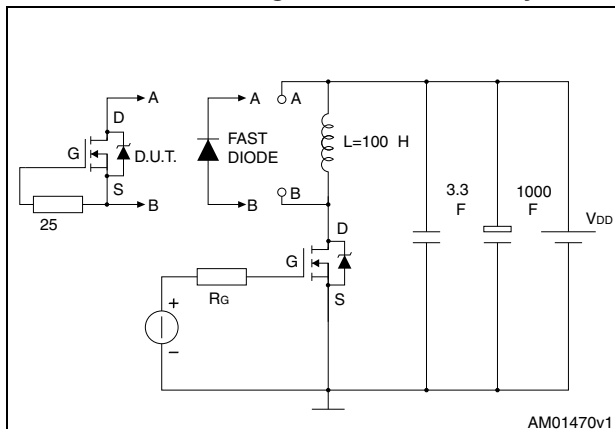
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Figure 20. Gate charge test circuit



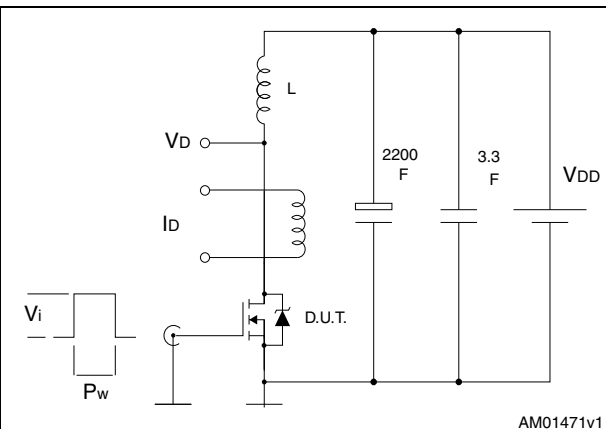
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Figure 21. Test circuit for inductive load switching and diode recovery times



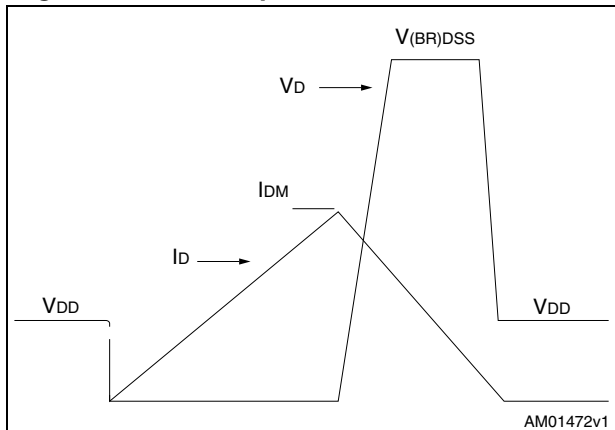
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Figure 22. Unclamped inductive load test circuit



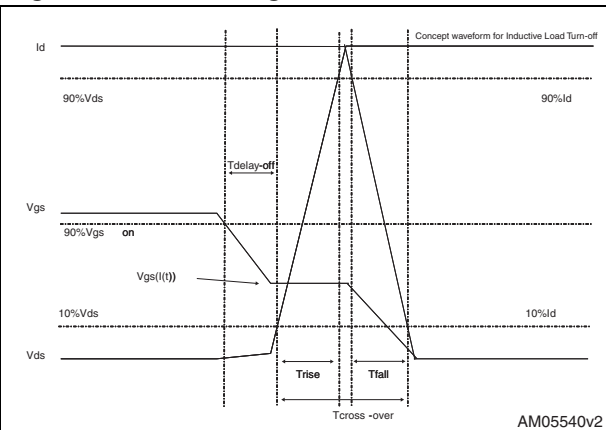
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Figure 23. Unclamped inductive waveform



AM01472v1

Figure 24. Switching time waveform



AM05540v2

4 **Package mechanical data**

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 9. D²PAK (TO-263) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 25. D²PAK (TO-263) drawing

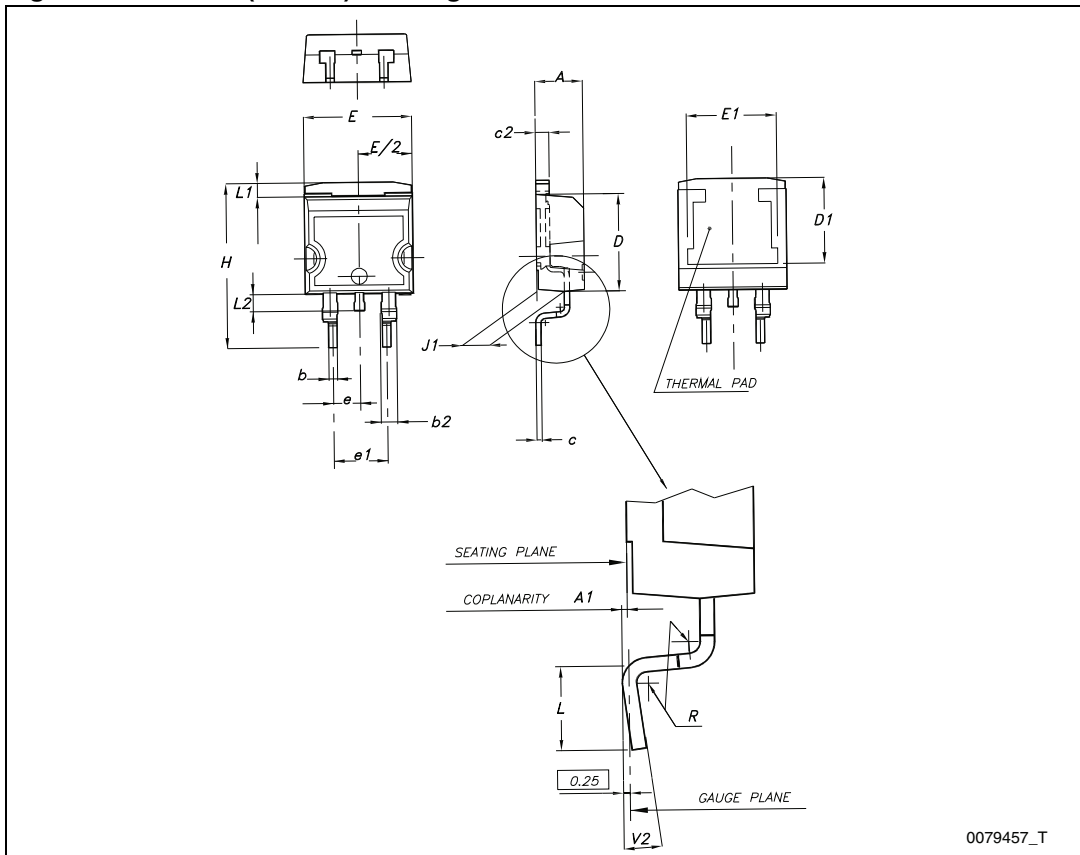
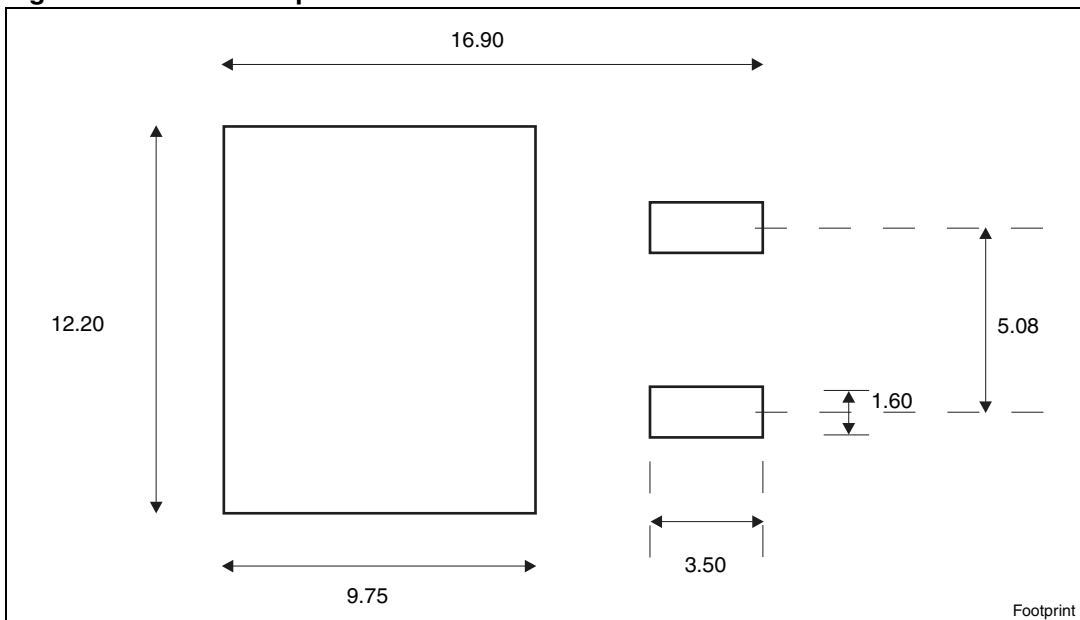


Figure 26. D²PAK footprint^(a)



a. All dimension are in millimeters

Table 10. DPAK (TO-252) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°

Figure 27. DPAK (TO-252) drawing

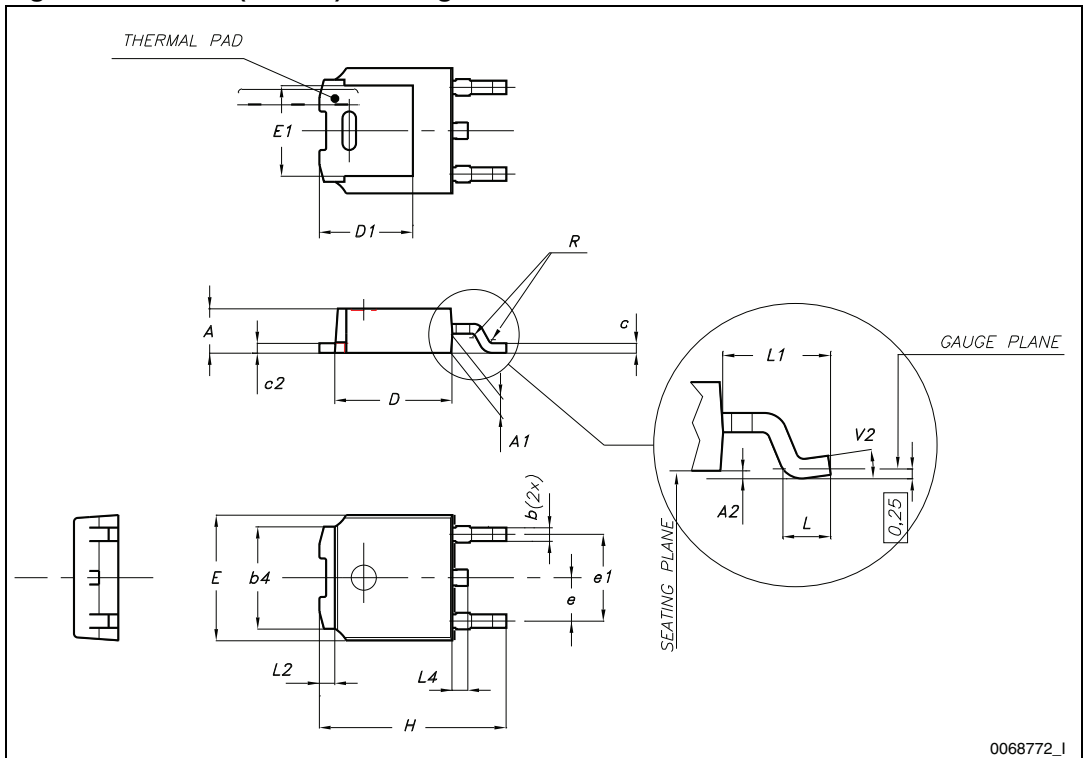
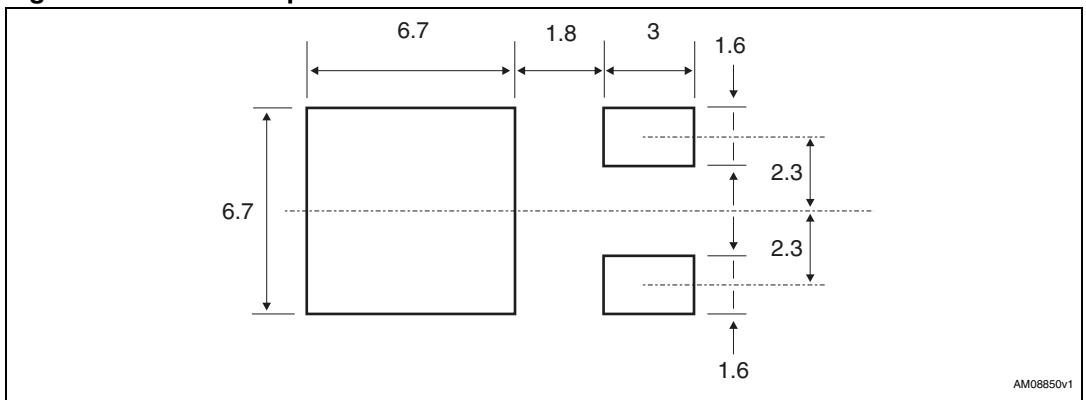


Figure 28. DPAK footprint^(b)



b. All dimensions are in millimeters

Table 11. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 29. TO-220FP drawing

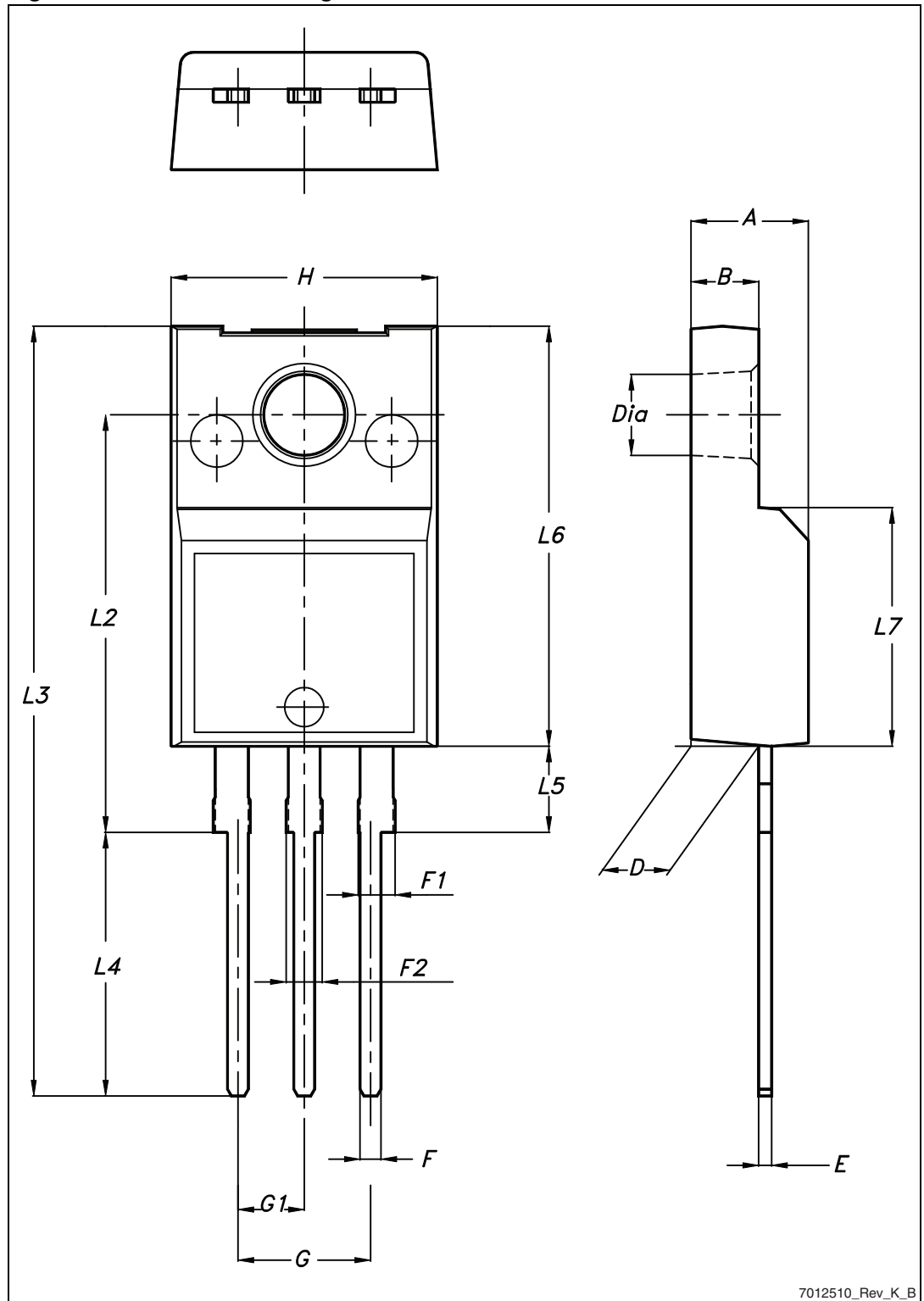


Table 12. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 30. TO-220 type A drawing

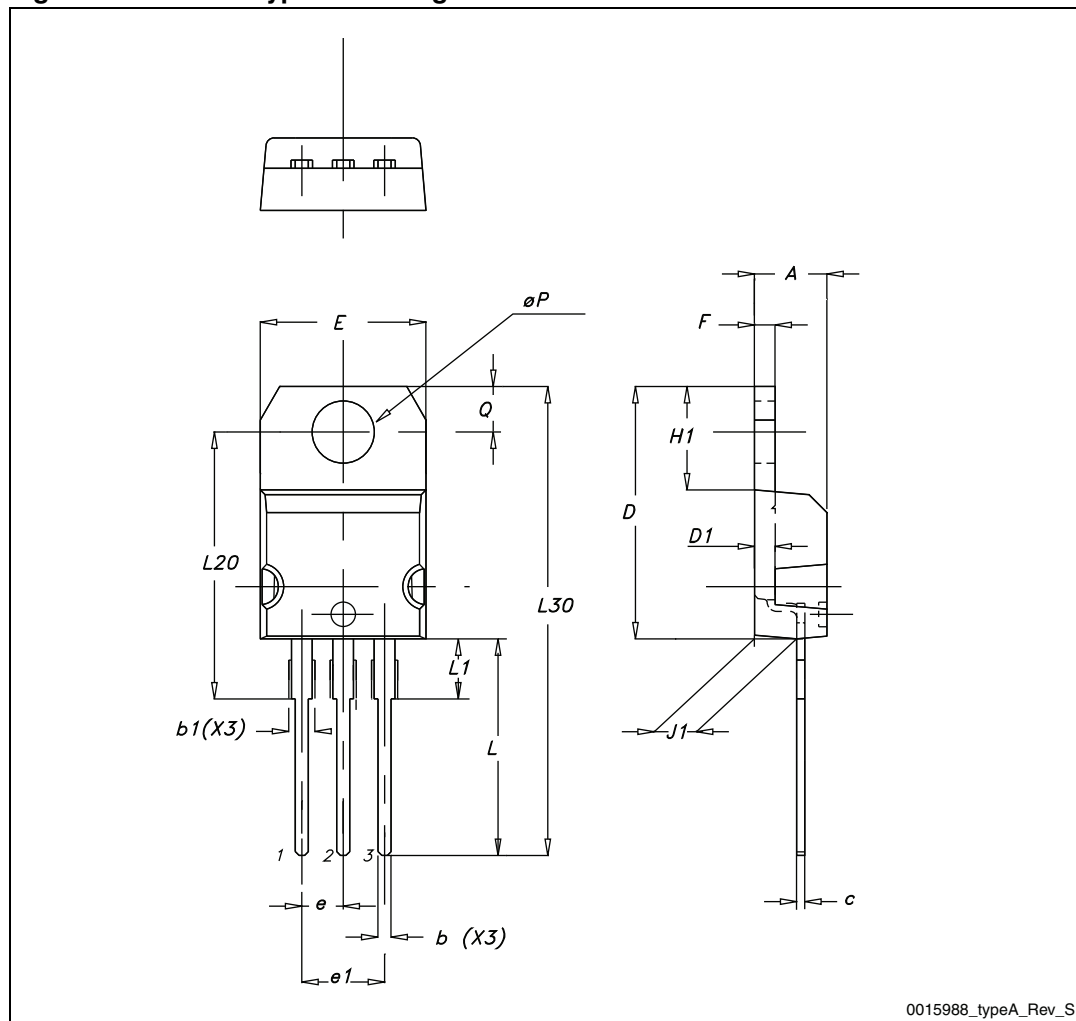
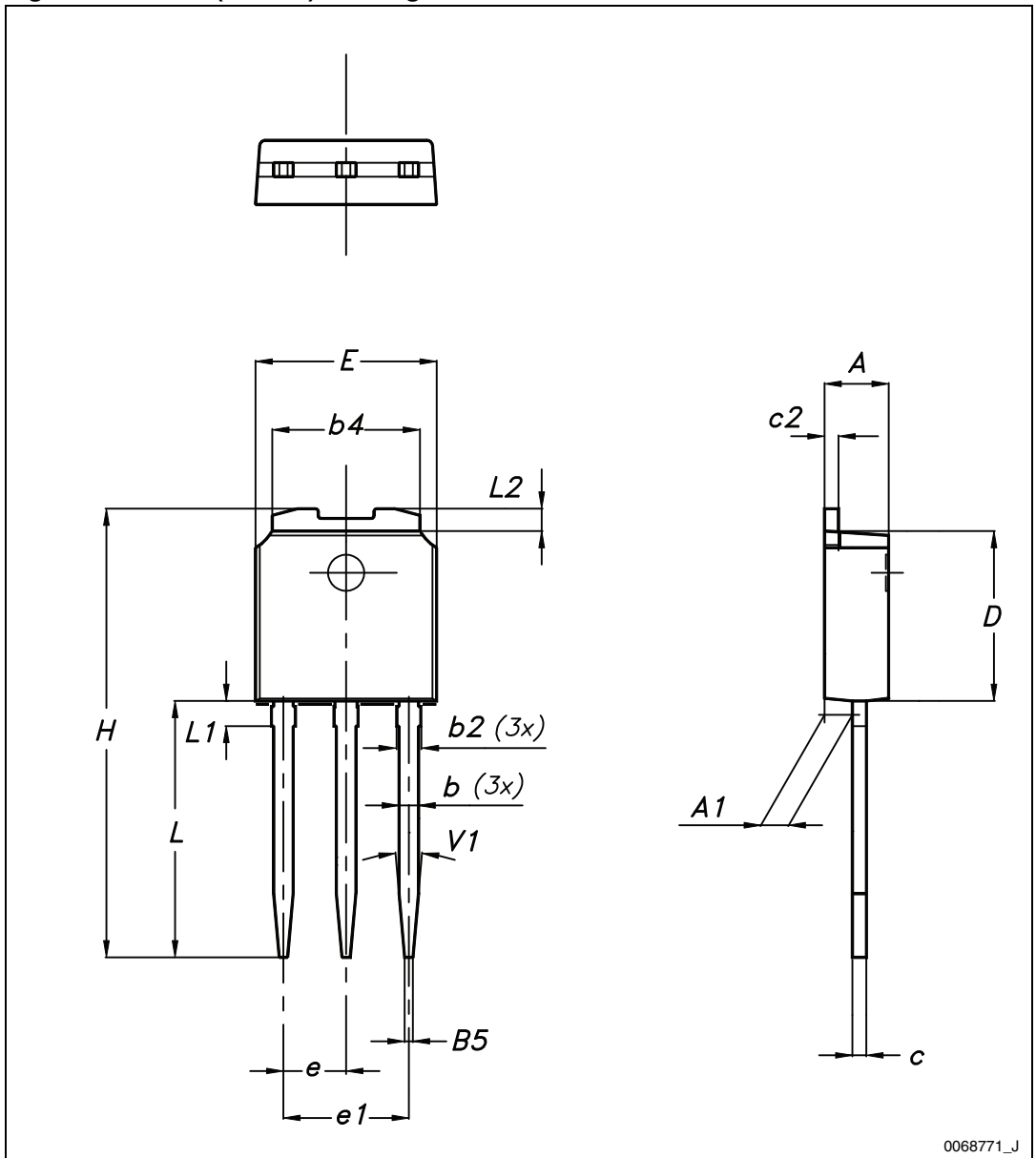


Table 13. IPAK (TO-251) mechanical data

DIM	mm.		
	min.	typ.	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.30	
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10°	

Figure 31. IPAK (TO-251) drawing



5 Packaging mechanical data

Table 14. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Table 15. D²PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base qty		1000
P2	1.9	2.1	Bulk qty		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Figure 32. Tape

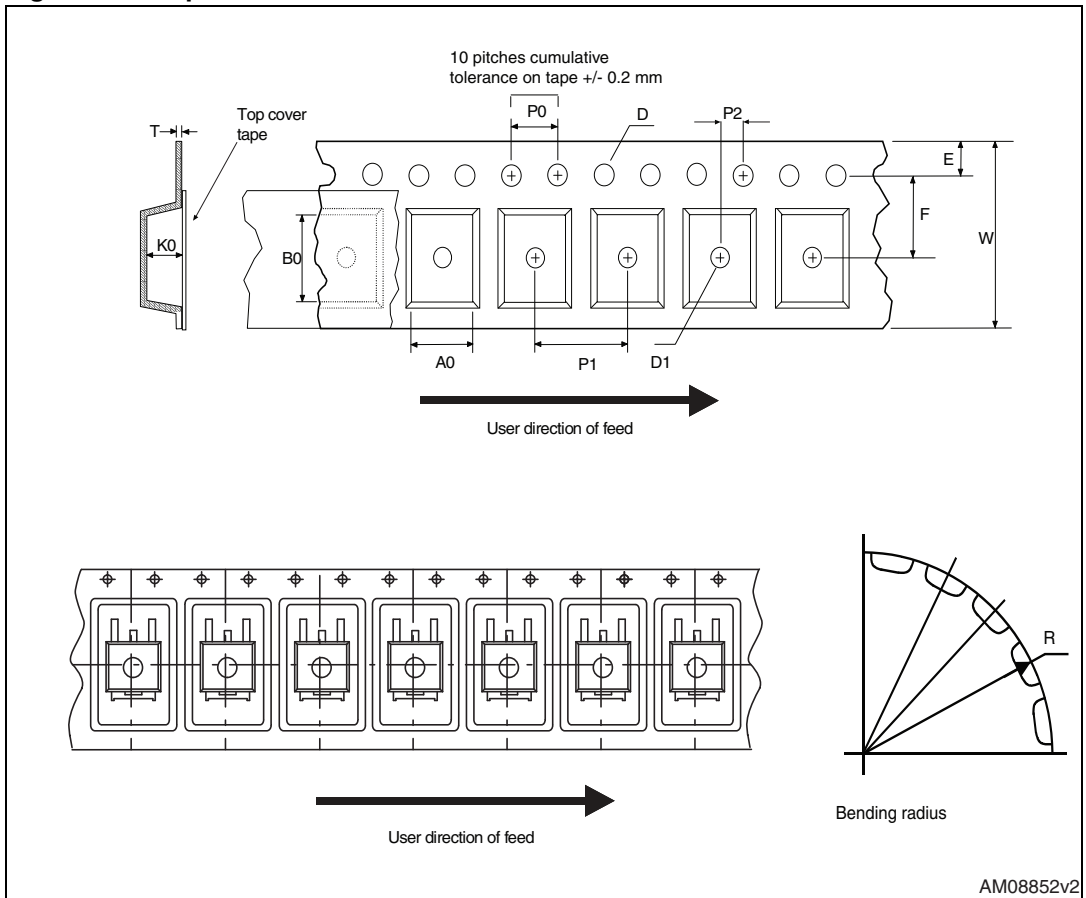
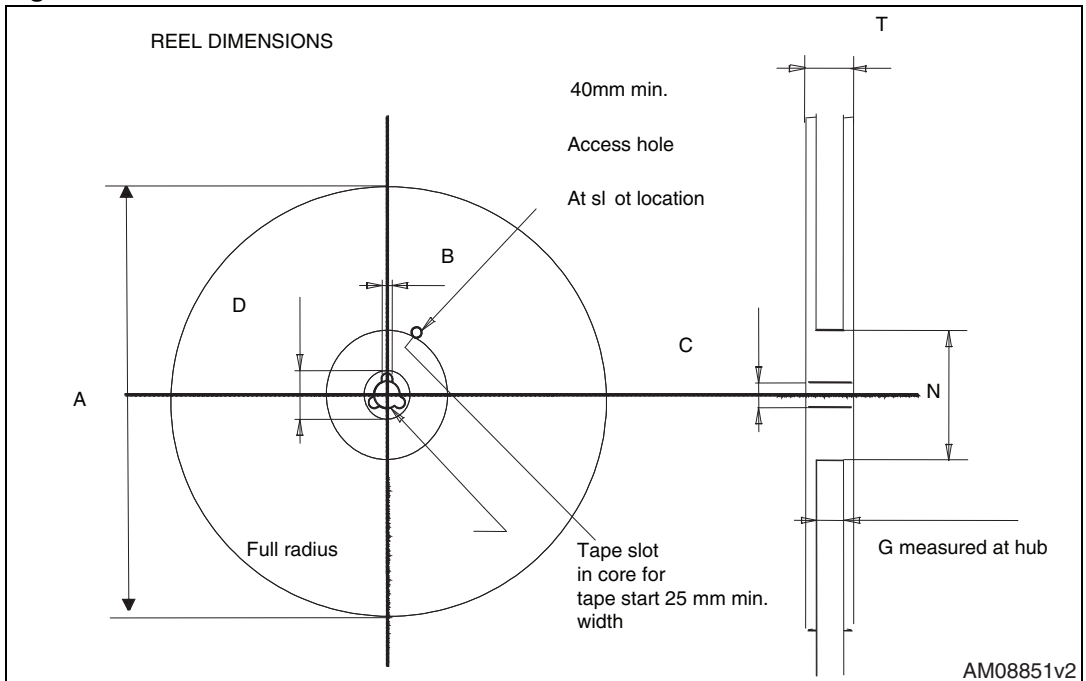


Figure 33. Reel



6 Revision history

Table 16. Document revision history

Date	Revision	Changes
23-Feb-2012	1	First release.
03-Dec-2012	2	<ul style="list-style-type: none">– Minor text changes in cover page– Added IPAK packages– Added Section 2.1: Electrical characteristics (curves)– Updated Section 5: Packaging mechanical data– Modified: note 2 on Table 2– Updated: mechanical data for TO-220FP package

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